

SURFACE MOUNT SMALL SIGNAL SCHOTTKY DIODE

VOLTAGE RANGE: 50 V CURRENT: 0.2 A

Features

- For general purpose applications
- This diode features very low turn-on voltage and fast switching. These devices are protected by a PN junction guard ring against excessive voltage, such as electrostatic discharges



Case: SOD-80/LL34, Glass

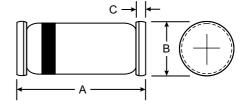
• Terminals: Solderable per MIL-STD-202,

Method 208

Polarity: Cathode BandWeight: 0.05 grams (approx.)







LL34/ SOD-80				
Dim	Min Max			
Α	3.30	3.70		
В	1.30	1.60		
С	0.28	0.50		
All Dimensions in mm				

Maximum Ratings and Electrical Characteristics T_A = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	Value	Unit
Continuous reverse voltage	V_R	50	V
Forward continuous current @ T _A =25°C	I _F	200 ¹⁾	mA
Peak forward current @ T _A =25 ℃	I _{FM}	500 ¹⁾	mA
Surge forw ard current @ t_p <1s, T_A =25 $^{\circ}$ C	I _{FSM}	5 ¹⁾	А
Power dissipation @ T _A =65 °C	P _{tot}	200 ¹⁾	mW
Junction temperature	T _J	125	°C
Ambient operating temperature range	T _A	-55+ 125	°C
Storage temperature range	T _{STG}	-55+ 150	$^{\circ}$

¹⁾ Valid provided that leads at a distance of 4mm from case are kept at ambient temperature

Characteristic	Symbol		Тур.	Max.	Unit
Reverse breakdown voltage	V _R	50.0			V
Forw ard voltage					
Pulse test tp<300 μ s, δ <2%					
@ I ₌ =0.1mA				0.30	V
@ I _F =1mA	V _F			0.38	V
@ I _F =10mA				0.45	V
@ I _F =30mA				0.60	V
@ I _F =100mA				0.90	V
Leakage current V _R =40V	I _R			5.0	μ А
Diode capacitance at V _R =1V,f=1MHz	C _d			8	pF
Reverse recovery time @ I _F =10mA,I _R =10mA,I _R =1mA	t _{rr}			5	ns
Thermal resistance junction to ambient	$R_{\theta JA}$			430 ¹⁾	°CW

¹⁾ Valid provided that leads at a distance of 4mm from case are kept at ambient temperature



FIG.1-ADMISSIBLEPOWERDISSIPATIONVS. AMBIENT TEMPERATURE

200 Jower 100 200

 T_A -Ambient temperature($^{\circ}$ C)

FIG. 3 - TYPICAL REVERSE CHARACTERISTICS

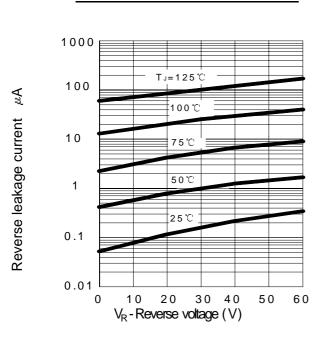
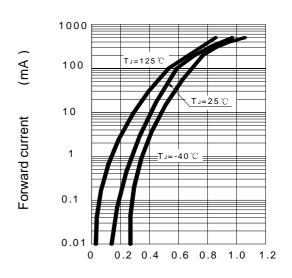
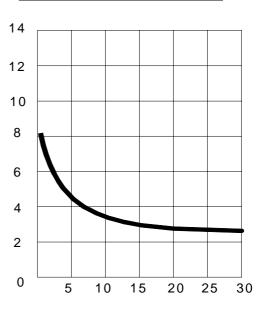


FIG. 2-TYPICAL INSTANTANEOUS FORWORD CHARACTERISTICS



V_F-Forward Voltage (V)

FIG.4 - TYPICAL JUNCTION CAPACITANCE



V_R-Reverse voltage (V)

Diode capacitance (pF)